

In The Specification

Paragraph beginning at line 12 of page 1 has been amended
as follows:

G1
-A frequently used fabrication technique in the manufacture of semiconductor devices involves the deposition of a metallic layer on the surface of a wafer. The deposition process utilizes a thin metal coating to cover steps such as in vias or contact holes that have diameters in the submicron range. The process is essential for achieving precise pattern alignment and reliability in fabricating VLSI (very large scale integration) and ULSI (ultra-large scale integration) devices.-

Paragraph beginning at line 5 of page 2 has been amended
as follows:

G2
-A conventional sputter apparatus that is used to fill trenches or contact holes arranged in a cluster form is shown in Figure 1. The cluster tool 10 consists of four physical

G2

vapor deposition chambers 12, 14, 16 and 18 arranged surrounding a transfer chamber 20. On the other end of the cluster tool 10, a number of auxiliary chambers 22, 24, 26 and 28 are arranged surrounding a buffer chamber 30. Further surrounding and in fluid communication with the buffer chamber 30 are the load lock chambers 36 and 38. The buffer chamber 30 and the transfer chamber 20 are both equipped with a wafer transfer robot 32 which is equipped with a robot blade 34. The cluster tool 10 is mounted in a wafer fabrication facility by through-the-wall installation such that the load lock chambers 36, 38 face the clean room and the process chambers 12~18 are located in a service area. The load lock chambers 36, 38 are used for load and unload wafers into and out of the cluster tool by a machine operator.-
